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According to the embodiment of Fig. 6, two mounting pads 2 are disposed on the substrate 1 to oppose each other. On an inner side of each pad 2, a trapezoidal solder resist 2 is fabricated. In the contour of the resist 2, a lower edge 10 on the side of the pad 3 is longer than an upper edge 9 on the side of a central section of the substrate 1, and the upper and lower edges 9, 10 are parallel to the pad 3. Moreover, on an inner side of the remaining edges which oppose each other, a triangular solder resist 11 is arranged. The triangle 11 includes a bottom edge 12 on a peripheral side of the substrate 1 and a vertex 13 opposing the bottom edge 12 on a central section of the substrate 1.

IN THE CLAIMS

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1. (Amended) A semiconductor mounting device comprising:

a plurality of solder resists positioned on a substrate between a pair of mounting pad lines, at least a pair of said plurality of solder resists being set up nearly parallel to each mounting pad line;

each solder resist extending toward end portions of said mounting pad lines so as to spread a sealing resin uniformly toward corners defined by said mounting pad line end portions when said semiconductor device is set on said mounting pad lines.

2. (Amended) A semiconductor mounting device comprising:

a plurality of solder resists positioned on a substrate between a pair of mounting pad lines, at least a pair of said plurality of solder resists being set up nearly parallel to each mounting pad line; and

a plurality of channels each defined between adjacent solder resists;

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said channels serving to feed a sealing resin [when said semiconductor device is set on said mounting pad lines uniformly toward corners defined by said mounting pad line end portions.

Cancel claim 3 without prejudice.

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4. A semiconductor mounting device comprising:
a plurality of solder resists positioned on a substrate between two pairs of mounting pad lines, a solder resist set up nearly parallel to each mounting pad;
a plurality of channels each defined between adjacent solder resists, said channels positioned diagonally with respect to the mounting pad lines;
said channels serving to feed a sealing resin when said semiconductor device is set on said mounting pad lines uniformly toward corners defined by said mounting pad line end portions.

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6. (Amended) The semiconductor mounting method in accordance with claim 5, wherein the solder resist zones have a thickness ranging from 10 μm to 30 μm .

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8. (Amended) The semiconductor device mounting method in accordance with claim 5, wherein the solder resist zones have a thickness ranging from 10 μm to 30 μm and the sealing resin is an epoxy-based instantaneous thermosetting resin having a contraction ration and an expansion ratio of cured resin, the contraction ratio larger than the expansion ratio.

9. (Amended) A semiconductor device mounting method in which on a substrate on which a mounting pad including a mounting section is formed interior to the mounting pad, sealing resin is supplied by one-point coating onto a central position of the mounting

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section, a semiconductor device including a plurality of projected electrodes is placed on the substrate, and the resin is heated under a predetermined pressure to thereby mount the semiconductor device onto the substrate, comprising the steps of:

arranging in the mounting section a plurality of solder resist zones to orient a flow of the sealing resin in a predetermined direction, the zones projecting upward;

mounting the semiconductor device on the mounting section and supplying thereby the sealing resin in a circumferential area of the semiconductor device mounted on the substrate;

forming with the sealing resin a filet in the circumferential area, the filet being uniform in quantity of resin; wherein

the solder resist zones each has a rectangular contour, and

are each parallel to an edge of the semiconductor device mounted on the substrate.

10. (Amended) The semiconductor device mounting method in accordance with claim 9, wherein the solder resist zones have a thickness ranging from 10 μm to 30 μm .

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12. (Amended) The semiconductor device mounting method in accordance with claim 9, wherein the solder resist zones have a thickness ranging from 10 μm to 30 μm and the sealing resin is a epoxy-based instantaneous thermosetting resin having a contraction ratio and an expansion ratio of cured resin, the contraction ratio larger than the expansion ratio.

13. (Amended) A semiconductor device mounting method in which on a substrate on which a mounting pad including a mounting section is formed interior to the mounting pad, sealing resin is supplied by one-point coating onto a central position of the

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mounting section, a semiconductor device including a plurality of projected electrodes is placed on the substrate, and the resin is heated under a predetermined pressure to thereby mount the semiconductor device onto the substrate, comprising the steps of:

arranging in the mounting section a plurality of solder resist zones to orient a flow of the sealing resin in a predetermined direction, the zones projecting upward;

mounting the semiconductor device on the mounting section and supplying thereby the sealing resin in a circumferential area of the semiconductor device mounted on the substrate;

forming with the sealing resin a filet in the circumferential area, the filet being uniform in quantity of resin; wherein

the solder resist zones each has a trapezoidal contour,

the trapezoidal contour including a lower edge on an outer side of the mounting section and an upper edge on a central side of the mounting section, the upper edge being longer than the lower edge,

the upper and lower edges being parallel to an associated edge of the semiconductor device mounted on the substrate.

14. (Amended) The semiconductor device mounting method in accordance with claim 13, wherein the solder resist zones have a thickness ranging from 10 μm to 30 μm .

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16. (Amended) The semiconductor device mounting method in accordance with claim 13, wherein the solder resist zones have a thickness ranging from 10 μm to 30 μm and the sealing resin is an epoxy-based instantaneous thermosetting resin having a

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contraction ratio and an expansion ratio of cured resin, the contraction ratio larger than the expansion ratio.

17. (Amended) A semiconductor device mounting method in which on a substrate on which a mounting pad including a mounting section is formed interior to the mounting pad, sealed resin is supplied by one-point coating onto a central position of the mounting section, a semiconductor device including a plurality of projected electrodes is placed on the substrate, and the resin is heated under a predetermined pressure to thereby mount the semiconductor device onto the substrate, comprising the steps of:

arranging in the mounting section a plurality of solder resist zones to orient a flow of the sealing resin in a predetermined direction, the zones projecting upward;

mounting the semiconductor device on the mounting section and supplying thereby the sealing resin in a circumferential area of the semiconductor device mounted on the substrate;

forming with the sealing resin a fillet in the circumferential area, the fillet being uniform in quantity of resin; wherein

two opposing solder resist zones each has a trapezoidal contour,

each trapezoidal contour including a lower edge on an outer side of the mounting section and an upper edge on a central side of the mounting section, the lower edge being longer than the upper edge,

the upper and lower edges being parallel to a major edge of a rectangular contour of the semiconductor device mounted on the substrate,

and wherein two opposing solder resist zones each has a triangular contour,